

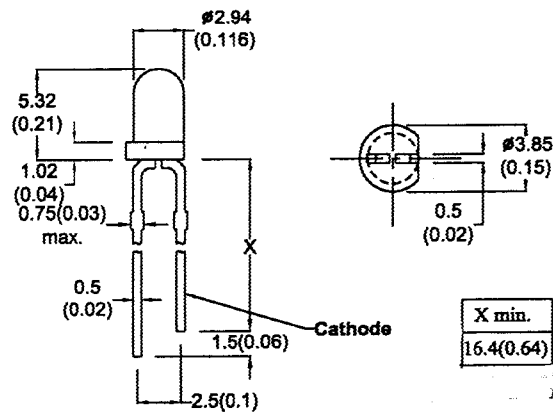
# MICRO ELECTRONICS

MI32T

INFRARED  
EMITTING  
DIODE

## DESCRIPTION

MI32T is GaAlAs infrared emitting diode molded in 3mm diameter clear transparent lens.



- All dimension in mm(inch)
- No Scale
- Tol. : +/-0.3mm

## ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	160mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

\* Pulse Width = 10μs, Duty Ratio = 0.01.

## ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	P <sub>o</sub>		0.5		mW	I <sub>F</sub> =20mA
Forward Voltage	V <sub>F</sub>			1.6	V	I <sub>F</sub> =20mA
Reverse Current	I <sub>R</sub>			100	μA	V <sub>R</sub> =5V
Half Intensity Beam Angle	θ <sub>HI</sub>		35		degree	I <sub>F</sub> =20mA
Peak Wavelength	λ <sub>p</sub>		940		nm	I <sub>F</sub> =20mA
Spectrum Line Half Width	Δλ		45		nm	I <sub>F</sub> =20mA



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